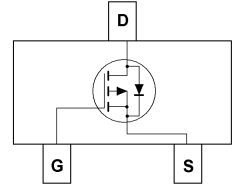


P-Channel Enhancement Mode MOSFET

Feature

- 18V/-3A, $R_{DS(ON)} = 120\text{m}\Omega(\text{MAX}) @V_{GS} = -4.5\text{V}$.
 $R_{DS(ON)} = 150\text{m}\Omega(\text{MAX}) @V_{GS} = -2.5\text{V}$.
- Super High dense cell design for extremely low $R_{DS(ON)}$
- Reliable and Rugged
- SOT-23 for Surface Mount Package



Applications

- Power Management
Portable Equipment and Battery Powered Systems.

SOT-23

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ Unless Otherwise noted

| Parameter | Symbol | Limit | Units |
|--------------------------|----------|----------|-------|
| Drain-Source Voltage | V_{DS} | -18 | V |
| Gate-Source Voltage | V_{GS} | ± 10 | V |
| Drain Current-Continuous | I_D | -3 | A |

Electrical Characteristics $T_A=25^\circ\text{C}$ Unless Otherwise noted

| Parameter | Symbol | Test Conditions | Min | Typ. | Max | Units |
|---|--------------|---|------|------|------|------------------|
| Off Characteristics | | | | | | |
| Drain to Source Breakdown Voltage | BVDSS | $V_{GS}=0\text{V}, I_D=-250\mu\text{A}$ | -18 | - | - | V |
| Zero-Gate Voltage Drain Current | IDSS | $V_{DS}=-18\text{V}, V_{GS}=0\text{V}$ | - | - | -1 | μA |
| Gate Body Leakage Current, Forward | IGSSF | $V_{GS}=10\text{V}, V_{DS}=0\text{V}$ | - | - | 100 | nA |
| Gate Body Leakage Current, Reverse | IGSSR | $V_{GS}=-10\text{V}, V_{DS}=0\text{V}$ | - | - | -100 | nA |
| On Characteristics | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{GS}=V_{DS}, I_D=-250\mu\text{A}$ | -0.4 | - | -1.0 | V |
| Static Drain-source On-Resistance | $R_{DS(ON)}$ | $V_{GS}=-4.5\text{V}, I_D=-3.0\text{A}$ | - | -- | 120 | $\text{m}\Omega$ |
| | | $V_{GS}=-2.5\text{V}, I_D=-2.0\text{A}$ | - | -- | 150 | $\text{m}\Omega$ |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| Drain-Source Diode Forward Voltage | VSD | $V_{GS}=0\text{V}, I_S=-1.25\text{A}$ | | | -1.2 | V |

Typical Characteristics

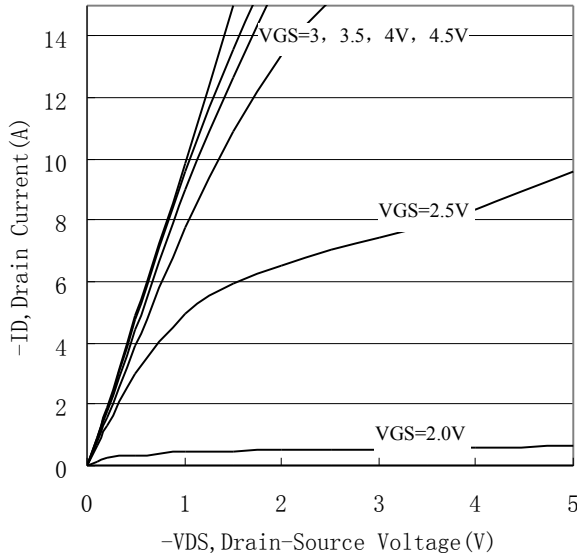


Figure 1. Output Characteristics

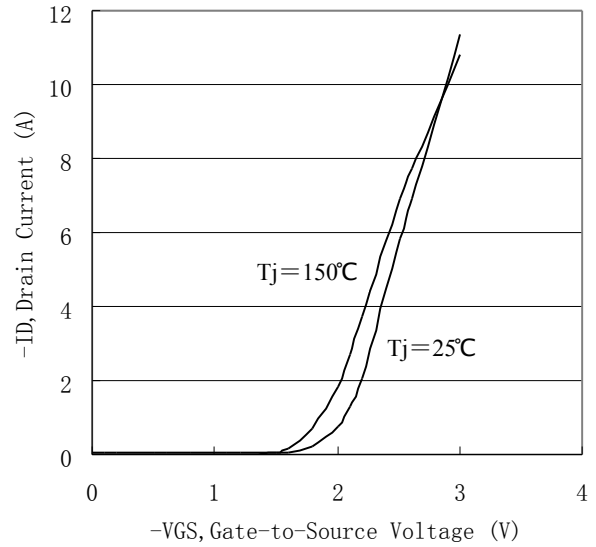


Figure 2. Transfer Characteristics

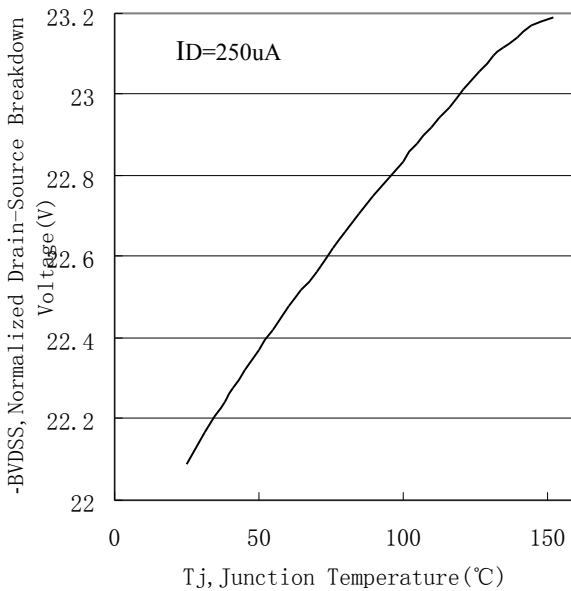


Figure 3. Breakdown Voltage Variation with Temperature

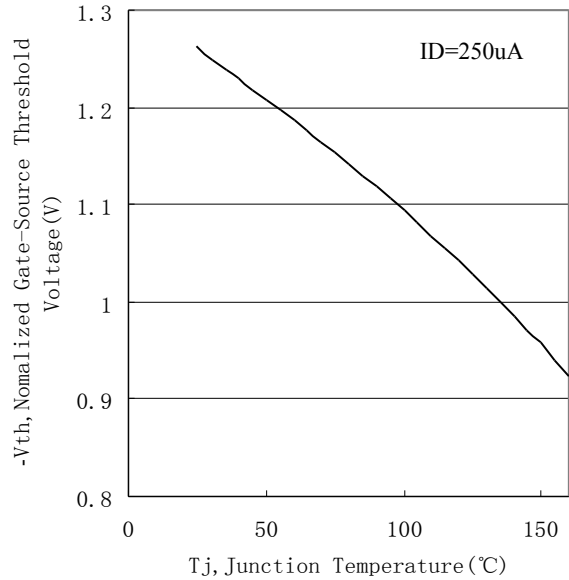


Figure 4. Gate Threshold Variation with Temperature

Typical Characteristics

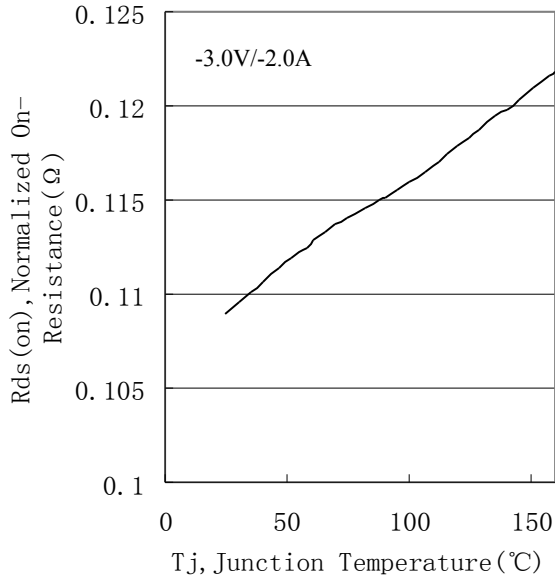


Figure 5. On-Resistance Variation with Temperature

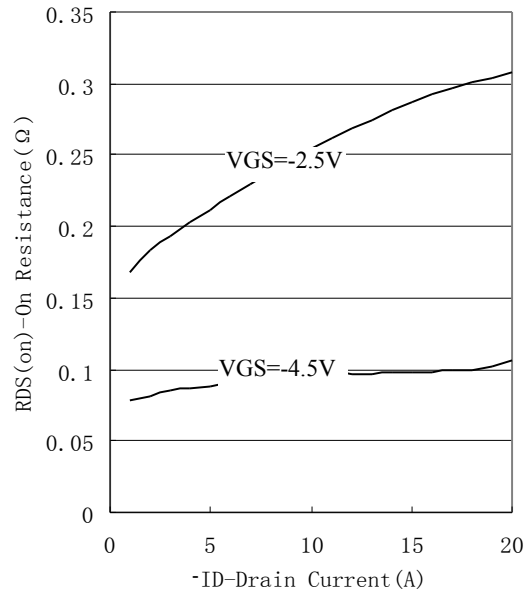


Figure 6. On-Resistance vs. Drain Current

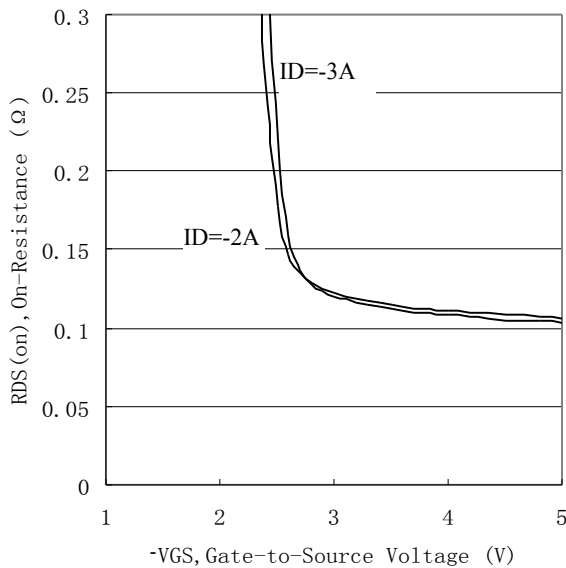


Figure 7. On-Resistance vs. Gate-to-Source Voltage

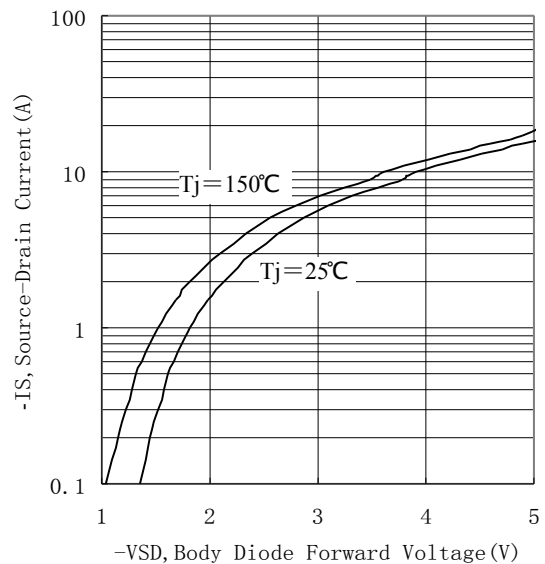
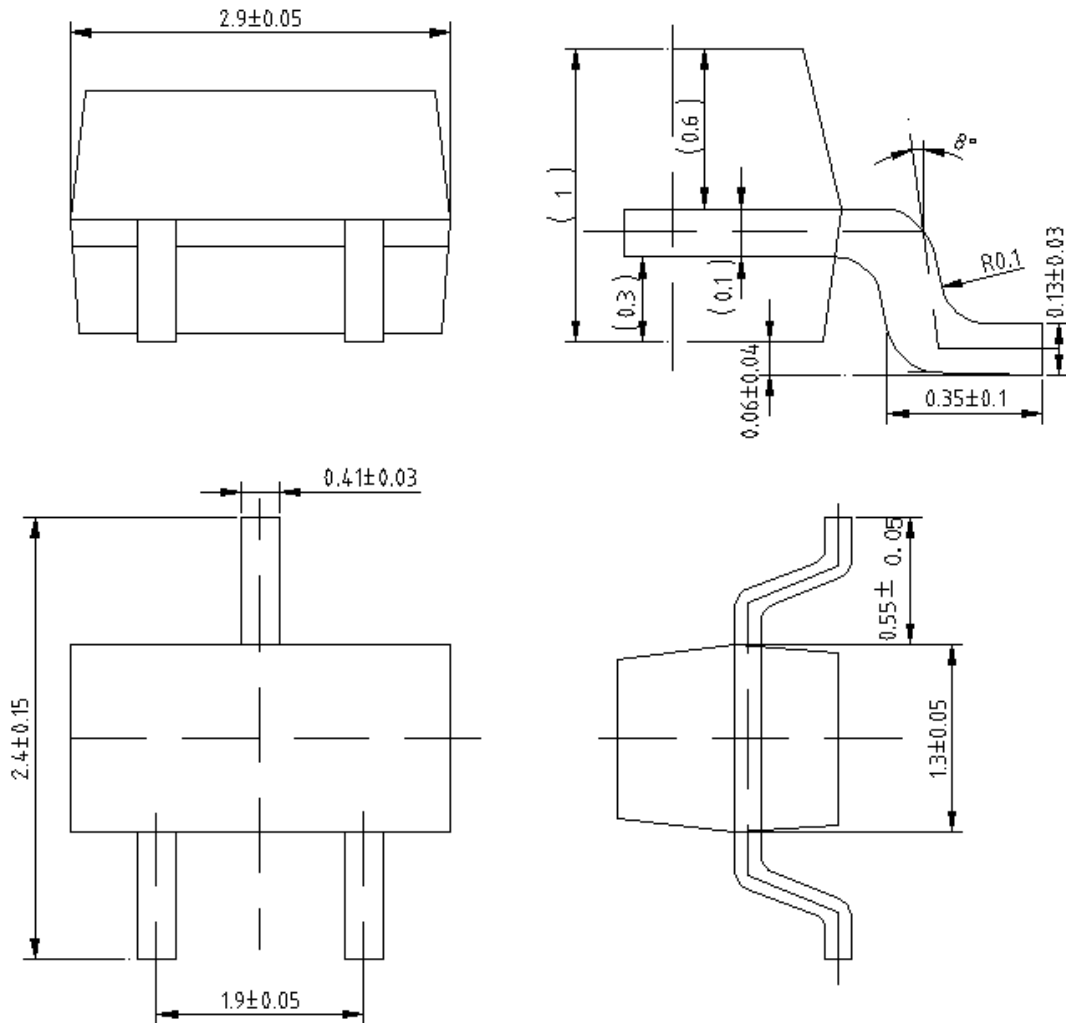


Figure 8. Source-Drain Diode Forward

Package Outline Dimensions (UNIT: mm)

SOT-23



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